



OK TO ENTER: /A.S./

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AF**PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: Valerie BOUSQUET, et al. Conf. No.: 7512
Application No.: 10/525,499 Examiner: Asok K. SARKAR
371(c) Date: September 21, 2005 Art Unit: 2891
Title: MBE GROWTH OF A SEMICONDUCTOR LAYER STRUCTURE
Atty. Dkt. No.: 24500-000015/US

Customer Service Window
Randolph Building
401 Dulany Street
Alexandria, VA 22314

August 19, 2009

Mail Stop AF**AMENDMENT UNDER 37 C.F.R. § 1.116**

Sir/Madam:

In response to the Final Office Action mailed May 22, 2009, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

Amendments to the Claims begin on page 2 of this paper.

Remarks begin on page 4 of this paper.

	Claims remaining after Amendment		Highest number previously paid for		Present extra
Total	4	-	20	=	0
Independent	1	-	3	=	0